

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Katsuya HASEGAWA et al  
Title: METHOD OF FORMING THIN FILM ON BASE SUBSTANCE VIA  
INTERMEDIATE LAYER  
Appl. No.: 10/526,745  
Filing Date: 03/07/2005  
Examiner: Unknown  
Art Unit: Unknown

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**  
**UNDER 37 CFR §1.56**

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Applicants herewith submit a Supplemental Information Disclosure Statement in order to correct minor typographical errors of the Information Disclosure Statement submitted on March 7, 2005. Since all of the references, with the exception of A12, were previously provided, only this reference is herein provided.

A copy of each non-U.S. patent document and each non-patent document is being submitted to comply with the provisions of 37 CFR §1.97 and §1.98.

The submission of any document herewith, which is not a statutory bar, is not intended as an admission that such document constitutes prior art against the claims of the present application or that such document is considered material to patentability as defined in 37 CFR §1.56(b). Applicants do not waive any rights to take any action which would be appropriate to antedate or otherwise remove as a competent reference any document which is determined to be a *prima facie* art reference against the claims of the present application.

**TIMING OF THE DISCLOSURE**

The listed documents are being submitted in compliance with 37 CFR §1.97(b), before the mailing of a first office action on the merits.

**RELEVANCE OF EACH DOCUMENT**

Documents A1 and A2 are U.S. counterparts of Document A4.

Documents A4-A10 and A12 were cited in the specification.

Documents A3 and [A8] A7 were cited as being relevant during the prosecution of the corresponding International application. A copy of the International Search Report is attached setting forth the portion of each document considered relevant by the examiner. An English translation each of the foreign language documents is not readily available; however English language abstracts are attached.

Applicants respectfully request that each listed document be considered by the Examiner and be made of record in the present application and that an initialed copy of Form PTO/SB/08 be returned in accordance with MPEP §609.

The Commissioner is hereby authorized to charge any additional fees which may be required regarding this application under 37 CFR §§ 1.16-1.17, or credit any overpayment, to Deposit Account No. 19-0741. Should no proper payment be enclosed herewith, as by a check being in the wrong amount, unsigned, post-dated, otherwise improper or informal or

even entirely missing, the Commissioner is authorized to charge the unpaid amount to  
Deposit Account No. 19-0741.

Respectfully submitted,

Date: August 3, 2005

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Substitute for form 1449B/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

Date Submitted: August 3, 2005

(use as many sheets as necessary)

Sheet 1 of 1

**Complete if Known**

Application Number	10/526,745
Filing Date	03/07/2005
First Named Inventor	Katsuya HASEGAWA
Group Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	017700-0174

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
	A1	2004/0224851	A	KAKIMOTO et al.	11-11-2004	
	A2	6,743,533	B1	KAKIMOTO et al.	06-01-2004	
	A3	5,607,899		YOSHIDA et al.	03-04-1997	

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
	A4	JP	2000-299026		FUJIKURA LTD.	10-24-2000		A
	A5	JP	07-291626		SUMITOMO ELECTRIC IND. LTD.	11-07-1995		A

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>6</sup>
	A6	"Material Engineering for Studying with Personal Computer," The 2001 Seminar of Japan Institute of Metals, November 2001, pp. 21-31.	
	A7	K. HASEGAWA et al., "Preparation of SmBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> Films With Improved In-plane Alignment by Pulsed Laser Deposition," J. Japan Inst. Metal., Vol. 66, 2002, pp. 320-328.	
	A8	M. NAKAMURA et al., "Fabrication of Single Crystal of SmBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-x</sub> by the Modified Top-Seeded Solution Growth Method in Low Oxygen Partial Pressure Atmosphere, Japan J. of Applied Phys., Vol. 34, 1995, pp. 6031-6035.	
	A9	T. MURATA et al., "Interface Structures in NdBCO/MgO and YBCO/MgO Superconducting Films Grown by LPE Method," The Fourth Pacific Rim International Conference [of] on Advanced Materials and Processing, 2001, pp. 729-732, The Japan Institute of Metals.	
	A10	K. SUDOH et al., "Superconducting properties and surface morphology of SmBa <sub>2</sub> Cu <sub>3</sub> O <sub>6+δ</sub> thin films," Physica C, Vol. 357-360, 2001, pp. 1358-1360; Elsevier Science.	
	A11	Y. WU et al., "Atomic configurations of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-x</sub> /MgO interfaces," Physica C 371, 2002, pp. 309-314, Elsevier Science.	
	A12	Q.D. JIANG et al., "Surface Morphology and In-Plane-Epitaxy of SmBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-δ</sub> Films on SrTiO <sub>3</sub> (001) Substrates Studied by STM and Grazing Incidence X-ray Diffraction, Solid State Comm. 98:2, pp 157-161.	

Examiner  
SignatureDate  
Considered

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

<sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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